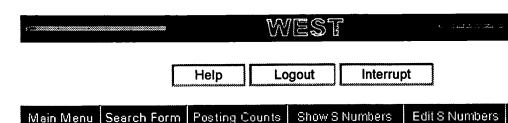
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Search Results -

Terms	Documents
12 and (integration or integrating) and 438/\$.ccls. and (distribute or distributing or	12
diffuse or diffusing)	12

US Patents Full Text Database
US Pre-Grant Publication Full-Text Database
JPO Abstracts Database
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Derwent World Patents Index
IBM Technical Disclosure Bulletins

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Refine Search: 12 and (integration or integrating) and 438/\$.ccls. and (distribute or distributing or diffuse or diffusing)

Search History

Today's Date: 4/21/2001

DB Name	<u>Ouery</u>	Hit Count	Set Name
USPT	12 and (integration or integrating) and 438/\$.ccls. and (distribute or distributing or diffuse or diffusing)	12	<u>L5</u>
USPT	12 and (integration or integrating) and 438/\$.ccls.	20	<u>L4</u>
USPT	12 and (integration or integrating)	43	<u>L3</u>
USPT	11 and conductivity and dielectric	150	<u>L2</u>
USPT	diode and (dopant or doping) and (cap or capping)and (implant or implanting) and mask	390	<u>L1</u>

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Search Results - Record(s) 1 through 12 of 12 returned.

1. Document ID: US 6136652 A

L6: Entry 1 of 12 File: USPT Oct 24, 2000

US-PAT-NO: 6136652

DOCUMENT-IDENTIFIER: US 6136652 A

TITLE: Preventing dielectric thickening over a channel area

of a split-gate transistor

Full Title Citation Front Review Classification Date Reference Claims KMC Draw Desc Image

2. Document ID: US 5851864 A

L6: Entry 2 of 12

File: USPT

Dec 22, 1998

US-PAT-NO: 5851864

DOCUMENT-IDENTIFIER: US 5851864 A

TITLE: Method of fabricating BiCMOS devices

Full Title Citation Front Review Classification Date Reference Claims KMC Draw. Desc Image

3. Document ID: US 5744384 A

L6: Entry 3 of 12 File: USPT

Apr 28, 1998

US-PAT-NO: 5744384

DOCUMENT-IDENTIFIER: US 5744384 A

TITLE: Semiconductor structures which incorporate thin film

transistors

Full Title Citation Front Review Classification Date Reference Claims KMC Draw Desc Image

4. Document ID: US 5643820 A

L6: Entry 4 of 12 File: USPT

Jul 1, 1997

US-PAT-NO: 5643820

DOCUMENT-IDENTIFIER: US 5643820 A

TITLE: Method for fabricating an MOS capacitor using zener

diode region

Full Title Citation Front Review Classification Date Reference Claims 1000C Draw Desc Image

5. Document ID: US 5393681 A

L6: Entry 5 of 12

File: USPT Feb 28, 1995

US-PAT-NO: 5393681

DOCUMENT-IDENTIFIER: US 5393681 A

TITLE: Method for forming a compact transistor structure

Full | Title | Citation | Front | Review | Classification | Date | Reference | Claims | KWIC | Draw Desc | Image

6. Document ID: US 5342794 A

L6: Entry 6 of 12 File: USPT

Aug 30, 1994

US-PAT-NO: 5342794

DOCUMENT-IDENTIFIER: US 5342794 A

TITLE: Method for forming laterally graded deposit-type

emitter for bipolar transistor

Full Title Citation Front Review Classification Date Reference Claims KMC Draw Desc Image

7. Document ID: US 5283202 A

L6: Entry 7 of 12 File: USPT

Feb 1, 1994

US-PAT-NO: 5283202

DOCUMENT-IDENTIFIER: US 5283202 A

TITLE: IGBT device with platinum lifetime control having gradient or profile tailored platinum diffusion regions

Full Title Citation Front Review Classification Date Reference Claims KMC Draw Desc Image

8. Document ID: US 5262336 A

L6: Entry 8 of 12 File: USPT

Nov 16, 1993

US-PAT-NO: 5262336

DOCUMENT-IDENTIFIER: US 5262336 A

TITLE: IGBT process to produce platinum lifetime control

Full | Title | Citation | Front | Review | Classification | Date | Reference | Claims | KWIC | Draw. Desc | Image 9. Document ID: US 5223449 A L6: Entry 9 of 12 File: USPT Jun 29, 1993 US-PAT-NO: 5223449 DOCUMENT-IDENTIFIER: US 5223449 A TITLE: Method of making an integrated circuit composed of group III-V compound field effect and bipolar semiconductors Full | Title | Citation | Front | Review | Classification | Date | Reference | Claims | KWIC | Draw. Desc | Image 10. Document ID: US 5075241 A L6: Entry 10 of 12 File: USPT Dec 24, 1991 US-PAT-NO: 5075241 DOCUMENT-IDENTIFIER: US 5075241 A TITLE: Method of forming a recessed contact bipolar transistor and field effect device Full Title Citation Front Review Classification Date Reference Claims KWIC Draw Desc Image 11. Document ID: US 4985744 A Jan 15, 1991 L6: Entry 11 of 12 File: USPT US-PAT-NO: 4985744 DOCUMENT-IDENTIFIER: US 4985744 A TITLE: Method for forming a recessed contact bipolar transistor and field effect transistor Full | Title | Citation | Front | Review | Classification | Date | Reference | Claims | KWIC | Draw, Desc | Image 12. Document ID: US 4849344 A L6: Entry 12 of 12 File: USPT Jul 18, 1989 US-PAT-NO: 4849344

DOCUMENT-IDENTIFIER: US 4849344 A

TITLE: Enhanced density modified isoplanar process

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15					12

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